# ELEC-313 Lab 3: Diode Circuits

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Date Performed: September 25, 2013 Partners: Charles Pittman

Stephen Wilson

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### 1 Objective

The objective is to observe the basic operation of a diode. In addition, the Schockley equation (Eq 2) is used to find the diode's reverse saturation current  $(I_S)$  and thermal voltage  $(V_T)$  using values measured in the lab.

### 2 Equipment

Diode: 1N4007 Power supply: HP E3631A Function generator: HP 33120A Resistors:  $47\,\Omega$  Multimeter: Fluke 8010A Capacitor:  $1\,\mu\text{F}$  Oscilloscope: Agilent 54622D

Resistive decade box: HeathKit IN-3117

### 3 Schematics

(a) Circuit used for Parts A andPart B.(b) Circuit used for Part C.

Figure 1: Circuits used in this lab.

#### 4 Procedure

#### 4.1 Rectifier

#### 4.2 Voltage Regulator

#### 5 Results

	Nominal	Measured	% Difference
	$(\Omega)$	$(\Omega)$	
$R_1$	470	465.3	1.00

Table 1: Comparison of nominal and measured resistance in Part A.

Figure 2: Diode characteristics measured in Parts A and B.

$R(\Omega)$	$V_d$ (V)	$I_d  (\mathrm{mA})$
200	0.751	46.00
500	0.713	18.60
1k	0.682	9.30
2k	0.650	4.70
5k	0.605	1.85
10k	0.571	0.94
20k	0.538	0.47
50k	0.494	0.19
100k	0.464	0.10

Table 2: Diode characteristics measured in Part B.

$$\frac{V_d \text{ (V)} \quad I_d \text{ (mA)} \quad V_{OC} \text{ (V)}}{0.712} \quad 27.2 \quad 6.70}$$

Table 3: Diode characteristics measured in Part C.

Table 4: Results from data analysis.

## 6 Conclusion

## 7 Equations

$$\%_{diff} = \frac{|nominal - measured|}{nominal} 100\%$$
 (1)

$$I_D = I_S \left( e^{\frac{V_D}{V_T}} - 1 \right) \tag{2}$$

$$m = \frac{\ln(I_2) - \ln(I_1)}{V_2 - V_1} = \frac{1}{V_T}$$
(3)